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November 2013

FQD7N10L

N-Channel QFET® MOSFET

100 V, 5.8 A, 350 $m\Omega$

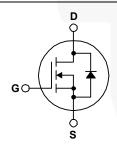
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 5.8 A, 100 V, $R_{DS(on)}$ = 350 m Ω (Max.) @ V_{GS} = 10 V, ID = 2.9 A
- Low Gate Charge (Typ. 4.6 nC)
- Low Crss (Typ. 12 pF)
- · 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQD7N10LTM	Unit
V_{DSS}	Drain-Source Voltage		100	V
I _D	Drain Current - Continuous (T _C = 25°C)		5.8	Α
	- Continuous (T _C = 100°C)		3.67	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	23.2	Α
V _{GSS}	Gate-Source Voltage		± 20	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		50	mJ
I _{AR}	Avalanche Current	(Note 1)	5.8	Α
E _{AR}	Repetitive Avalanche Energy (N		2.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns
P _D	Power Dissipation (T _A = 25°C) *		2.5	W
	Power Dissipation (T _C = 25°C)		25	W
	- Derate above 25°C		0.2	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQD7N10LTM	Unit
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	5.0	
В	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD7N10LTM	FQD7N10L	D-PAK	Tape and Reel	330 mm	16 mm	2500 units

Electrical Characteristics T_c = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		0.1		V/°C
I _{DSS}	Zana Cata Valtana Dunin Courset	V _{DS} = 100 V, V _{GS} = 0 V			1	μА
Zero Gate Voltage Drain Current	Zero Gate Voltage Drain Current	V _{DS} = 80 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V		-	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		2.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 2.9 \text{ A}$ $V_{GS} = 5 \text{ V}, I_D = 2.9 \text{ A}$		0.275 0.300	0.35 0.38	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 30 V, I _D = 2.9 A	\	4.6		S
	ic Characteristics			000	000	
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		220	290	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		55	72	pF
C _{rss}	Reverse Transfer Capacitance			12	15	pF
Switchi	ng Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 50 V, I _D = 7.3 A,		9	30	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		100	210	ns
t _{d(off)}	Turn-Off Delay Time			17	45	ns
t _f	Turn-Off Fall Time	(Note 4)		50	110	ns
Qg	Total Gate Charge	V _{DS} = 80 V, I _D = 7.3 A,		4.6	6.0	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 5 V		1.0		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		2.6		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Did				5.8	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				23.2	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 5.8 A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 7.3 A,		70		ns
Q _{rr}	Reverse Recovery Charge	dl _F / dt = 100 A/μs		140	//	nC

- **Notes:** 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 2.23 mH, I_{AS} = 5.8 A, V_{DD} = 25 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. I_{SD} ≤ 7.3 A, di/dt ≤ 300 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_{J} = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

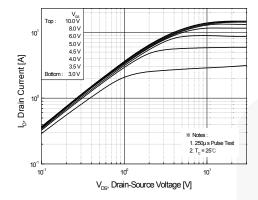


Figure 1. On-Region Characteristics

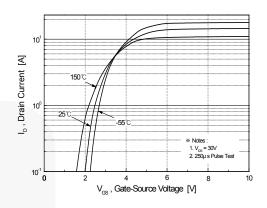


Figure 2. Transfer Characteristics

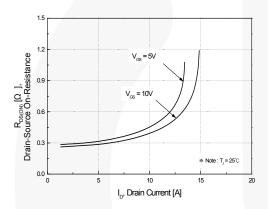


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

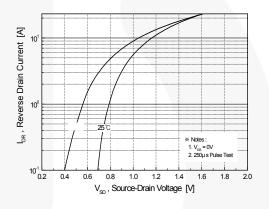


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

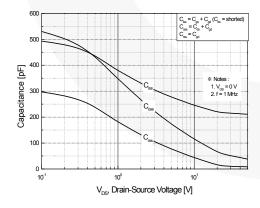


Figure 5. Capacitance Characteristics

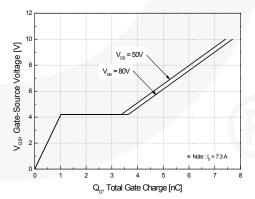


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

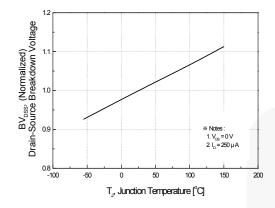
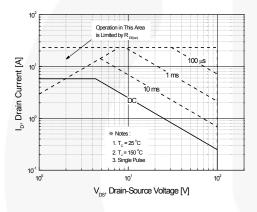


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



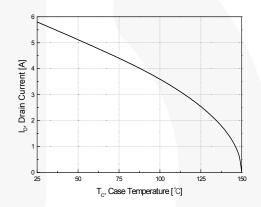


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

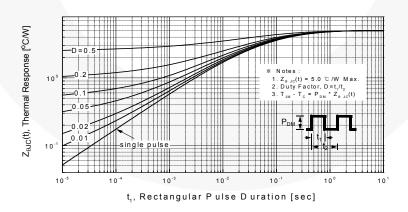


Figure 11. Transient Thermal Response Curve

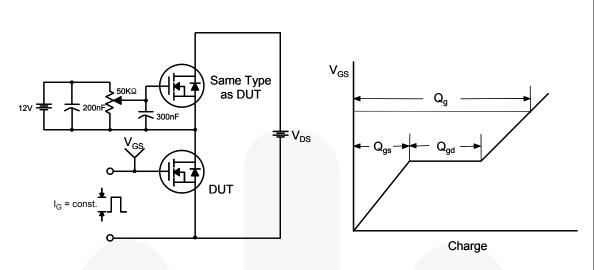


Figure 12. Gate Charge Test Circuit & Waveform

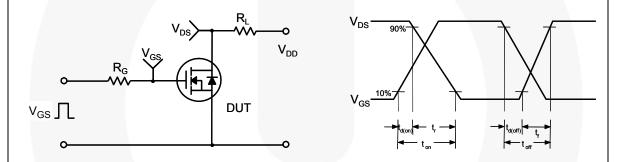


Figure 13. Resistive Switching Test Circuit & Waveforms

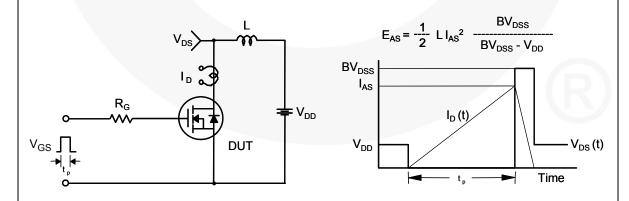
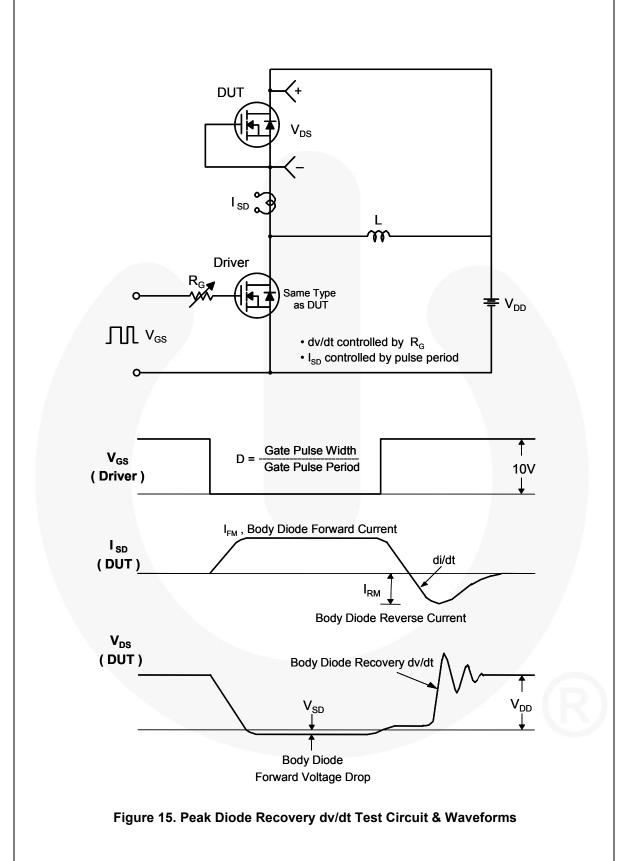


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

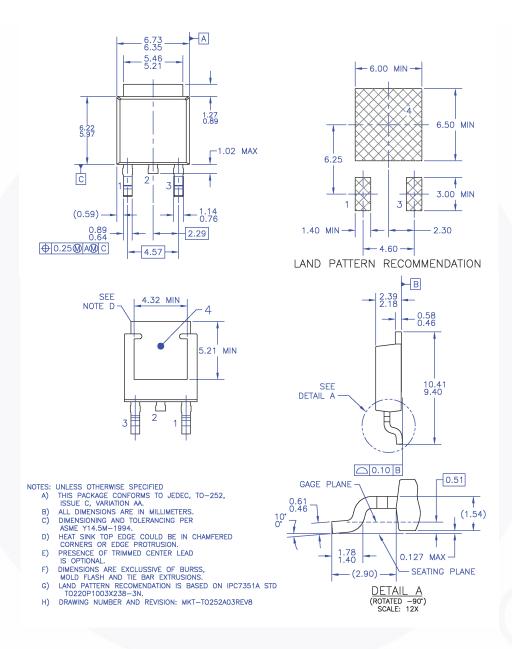


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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